Abstracts

A Silicon MOS Process for Integrated RF Power Amplifiers

C. Dragon, J. Costa, D. Lamey, D. Ngo, W. Burger and N. Camilleri. "A Silicon MOS Process for Integrated RF Power Amplifiers." 1996 MTT-S International Microwave Symposium Digest 96.1 (1996 Vol. I [MWSYM]): 257-260.

A silicon-based technology is presented which integrates passive components with a silicon Power MOSFET for use in Integrated Power Amplifiers at UHF, VHF, and RF frequencies. This low-cost process incorporates capacitors, inductors, resistors, ground vias, transmission lines, and an ESD protection diode. A design library containing models and layouts for the active and passive components was compiled.

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